

# 2SC5098

## SILICON NPN EPITAXIAL PLANAR TYPE TRANSISTOR

### TENTATIVE DATA

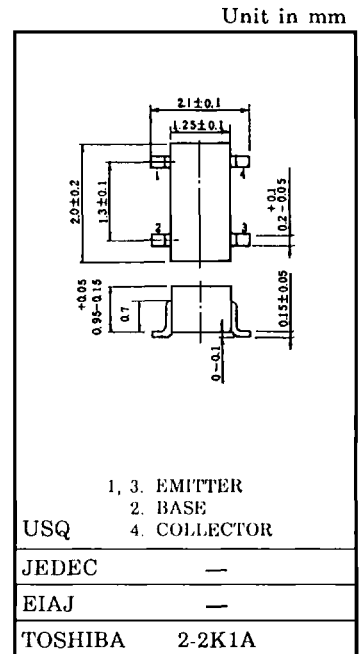
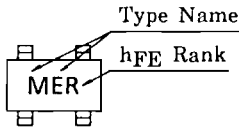
VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS.

- Low Noise Figure, High Gain.
- $NF = 1.8\text{dB}$ ,  $|S_{21e}|^2 = 9.5\text{dB}$  ( $f = 2\text{GHz}$ )

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	20	V
Collector-Emitter Voltage	$V_{CEO}$	10	V
Emitter-Base Voltage	$V_{EBO}$	1.5	V
Base Current	$I_B$	7	mA
Collector Current	$I_C$	15	mA
Collector Power Dissipation	$P_C$	100	mW
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55~125	$^\circ\text{C}$

### MARKING



Weight : 0.006g

MICROWAVE CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	$f_T$	$V_{CE} = 6\text{V}$ , $I_C = 7\text{mA}$	7	10	—	GHz
Insertion Gain	$ S_{21e} ^2 (1)$	$V_{CE} = 6\text{V}$ , $I_C = 7\text{mA}$ , $f = 1\text{GHz}$	—	15	—	dB
	$ S_{21e} ^2 (2)$	$V_{CE} = 6\text{V}$ , $I_C = 7\text{mA}$ , $f = 2\text{GHz}$	6.5	9.5	—	
Noise Figure	NF (1)	$V_{CE} = 6\text{V}$ , $I_C = 3\text{mA}$ , $f = 1\text{GHz}$	—	1.4	—	dB
	NF (2)	$V_{CE} = 6\text{V}$ , $I_C = 3\text{mA}$ , $f = 2\text{GHz}$	—	1.8	3.0	

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 10\text{V}$ , $I_E = 0$	—	—	1	$\mu\text{A}$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 1\text{V}$ , $I_C = 0$	—	—	1	$\mu\text{A}$
DC Current Gain	$h_{FE}$ (Note 1)	$V_{CE} = 6\text{V}$ , $I_C = 7\text{mA}$	50	—	160	—
Output Capacitance	$C_{ob}$	$V_{CB} = 10\text{V}$ , $I_E = 0$ , $f = 1\text{MHz}$	—	0.6	—	pF
Reverse Transfer Capacitance	$C_{re}$	(Note 2)	—	0.4	0.85	pF

(Note 1) :  $h_{FE}$  Classification R : 50~100, O : 80~160

(Note 2) :  $C_{re}$  is measured by 3 terminal method with capacitance bridge.